## Advance Information

# The RF Small Signal Line **GaAs MESFET AGC Amplifier**

The MRF9820T1 is a high performance GaAs AGC amplifier suitable for use in low noise front end amplifier or downconverter applications. The device contains two enhancement mode MESFETs connected in cascode to allow access to both gates for gain control or injection of LO signals. This device is well suited for low voltage, low current front—end applications such as paging, cellular, GSM, DECT, and other portable wireless systems.

- Low Noise Figure: 1.5 dB @ 940 MHz, 1 mA
- · Built In ESD Protection
- · Does Not Require a Negative Supply Voltage
- RF Power Gain 16 dB @ 940 MHz, 1 mA
- High Third Order Intercept Point
- Industry Standard SOT–143 Surface Mount Package
- Order MRF9820T1 for Tape and Reel Packaging.
   T1 Suffix = 3,000 Units per 8 mm, 7 inch Reel.

## MRF9820T1

SURFACE MOUNT LOW NOISE ENHANCEMENT MODE GaAs CASCODE



CASE 318A-05, STYLE 11 (SOT-143)

#### **MAXIMUM RATINGS**

Rating	Symbol	Value	Unit
Drain-Source Voltage	V <sub>DS</sub>	6	Vdc
Gate 1–Source Voltage	V <sub>G1S</sub>	-4	Vdc
Gate 2–Source Voltage	V <sub>G2S</sub>	-4	Vdc
Drain Current — Continuous	ID	IDSS	_
Total Device Dissipation @ T <sub>C</sub> = 75°C Derate above 75°C	P <sub>D</sub>	231 4.3	mW mW/°C
Storage Temperature Range	T <sub>stg</sub>	-55 to +150	°C
Operating Channel Temperature	T <sub>ch</sub>	150	°C

#### THERMAL CHARACTERISTICS

Rating		Max	Unit
Thermal Resistance, Channel to Case		325	°C/W

#### **ELECTRICAL CHARACTERISTICS** (T<sub>C</sub> = 25°C unless otherwise noted)

Characteristic	Symbol	Value	Unit
Gate 1 Leakage Current ( $V_{DS} = 2 \text{ V}$ , $V_{G1S} = 0.425 \text{ V}$ , $V_{G2S} = 1 \text{ V}$ )	l <sub>G1S</sub>	4	μА
Gate 2 Leakage Current ( $V_{DS} = 2 \text{ V}$ , $V_{G1S} = 0.5 \text{ V}$ , $V_{G2S} = 0.425 \text{ V}$ )	I <sub>G2S</sub>	4	μА
Threshold Voltage ( $V_{DS} = 3 \text{ V}, V_{G2S} = 1 \text{ V}, I_D = 1 \text{ mA}$ )	V <sub>th</sub>	275 (min) 425 (max)	mV
Gate 1–to–Source Cutoff Voltage ( $V_{DS}$ = 2 V, $V_{G2S}$ = 1 V, $I_{D}$ = 200 $\mu$ A)	VG1S(off)	100 (min) 360 (max)	mV
Gate 2–to–Source Cutoff Voltage ( $V_{DS}$ = 2 V, $V_{G1S}$ = 0.5 V, $I_{D}$ = 200 $\mu$ A)	VG2S(off)	10 (min) 370 (max)	mV
Forward Transconductance (V <sub>DS</sub> = 2 V, V <sub>G2S</sub> = 1 V, I <sub>D</sub> = 1 mA)	9m	9 (min)	mS
Drain-to-Source Leakage Current (VDS = 2 V, VG1S = 0 V, VG2S = 0 V)	I <sub>DS(off)</sub>	2 (max)	μΑ

 $NOTE - \underline{\textbf{CAUTION}} - MOS$  devices are susceptible to damage from electrostatic charge. Reasonable precautions in handling and packaging MOS devices should be observed.



## $\textbf{PERFORMANCE CHARACTERISTICS} \ (T_{C} = 25^{\circ}\text{C unless otherwise noted})$

Characteristic	Symbol	Value	Unit
RF Power Gain ( $V_{DS} = 3 \text{ V}, V_{G2} = 1.7 \text{ V}, I_{D} = 1 \text{ mA}, f = 940 \text{ MHz}$ )	G <sub>ps</sub>	14 (min)	dB
Noise Figure ( $V_{DS} = 3 \text{ V}, V_{G2} = 1.7 \text{ V}, I_D = 1 \text{ mA}, f = 940 \text{ MHz}$ )	NF	1.5 (typ) 2.0 (max)	dB
Input Third Order Intercept Point	IIP3	−3 (typ) −8 (min)	dBm

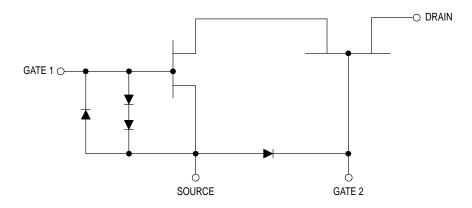


Figure 1. Electrical Schematic of GaAs AGC Amplifier

### **TYPICAL CHARACTERISTICS**

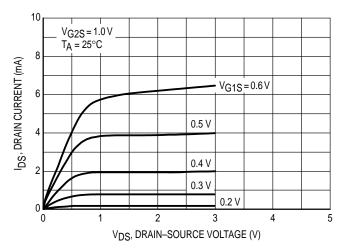


Figure 2. Drain Current versus V<sub>DS</sub>; Stepping V<sub>G1S</sub>

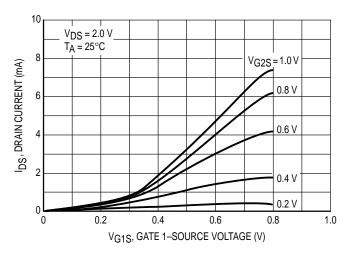


Figure 3. Drain Current versus VG1S; Stepping VG2S

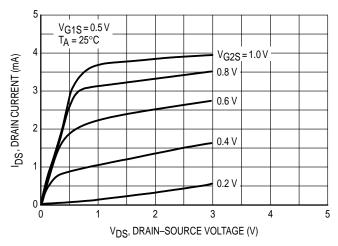


Figure 4. Drain Current versus V<sub>DS</sub>; Stepping V<sub>G2S</sub>

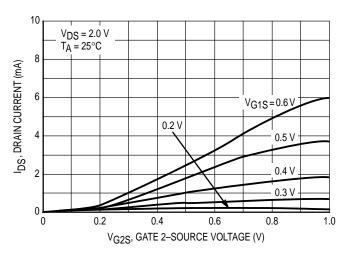
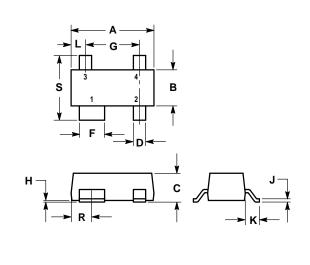


Figure 5. Drain Current versus VG2S; Stepping VG1S

#### PACKAGE DIMENSIONS



#### NOTES:

- DIMENSIONING AND TOLERANCING PER ANSI Y14.5M. 1982.
- 2. CONTROLLING DIMENSION: MILLIMETER.

	MILLIMETERS		INC	HES
DIM	MIN	MAX	MIN	MAX
Α	2.80	3.04	0.110	0.120
В	1.20	1.39	0.047	0.055
С	0.84	1.14	0.033	0.045
D	0.39	0.50	0.015	0.020
F	0.79	0.93	0.031	0.037
G	1.78	2.03	0.070	0.080
Н	0.013	0.10	0.0005	0.004
J	0.08	0.15	0.003	0.006
K	0.46	0.60	0.018	0.024
L	0.445	0.60	0.0175	0.024
R	0.72	0.83	0.028	0.033
S	2 11	2 48	0.083	0.098

STYLE 11:

PIN 1. SOURCE 2 GATE 1

2. GATE 1 3. GATE 2

4. DRAIN

CASE 318A-05 ISSUE R

Motorola reserves the right to make changes without further notice to any products herein. Motorola makes no warranty, representation or guarantee regarding the suitability of its products for any particular purpose, nor does Motorola assume any liability arising out of the application or use of any product or circuit, and specifically disclaims any and all liability, including without limitation consequential or incidental damages. "Typical" parameters which may be provided in Motorola data sheets and/or specifications can and do vary in different applications and actual performance may vary over time. All operating parameters, including "Typicals" must be validated for each customer application by customer's technical experts. Motorola does not convey any license under its patent rights nor the rights of others. Motorola products are not designed, intended, or authorized for use as components in systems intended for surgical implant into the body, or other applications intended to support or sustain life, or for any other application in which the failure of the Motorola product could create a situation where personal injury or death may occur. Should Buyer purchase or use Motorola products for any such unintended or unauthorized application, Buyer shall indemnify and hold Motorola and its officers, employees, subsidiaries, affiliates, and distributors harmless against all claims, costs, damages, and expenses, and reasonable attorney fees arising out of, directly or indirectly, any claim of personal injury or death associated with such unintended or unauthorized use, even if such claim alleges that Motorola was negligent regarding the design or manufacture of the part. Motorola and A are registered trademarks of Motorola, Inc. Motorola, Inc. is an Equal Opportunity/Affirmative Action Employer.

Mfax is a trademark of Motorola, Inc.

How to reach us:

**USA/EUROPE/Locations Not Listed**: Motorola Literature Distribution; P.O. Box 5405, Denver, Colorado 80217. 303–675–2140 or 1–800–441–2447

Mfax™: RMFAX0@email.sps.mot.com – TOUCHTONE 602–244–6609 – US & Canada ONLY 1–800–774–18 **JAPAN**: Nippon Motorola Ltd.: SPD, Strategic Planning Office, 4–32–1, Nishi–Gotanda, Shinagawa–ku, Tokyo 141, Japan. 81–3–5487–8488

TOUCHTONE 602–244–6609
 ASIA/PACIFIC: Motorola Semiconductors H.K. Ltd.; 8B Tai Ping Industrial Park,
 US & Canada ONLY 1–800–774–1848
 Ting Kok Road, Tai Po, N.T., Hong Kong. 852–26629298

MOTOROLA

INTERNET: http://motorola.com/sps

↑ MRF9820T1/D